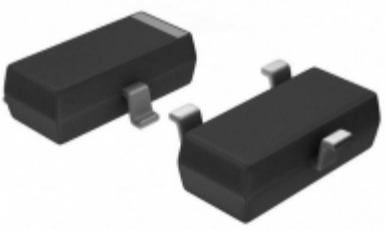


	<p>SI2327DS-T1-E3</p>
	<p>Hersteller-Teilenummer: SI2327DS-T1-E3</p>
	<p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p>
	<p>Teil der Beschreibung: MOSFET P-CH 200V 0.38A SOT23-3</p>
	<p>Datenblätter:  SI2327DS-T1-E3.pdf</p>
	<p>RoHs Status: Bleifrei / RoHS-konform</p>
<p>Image may be representation. See specs for product details.</p>	<p>Lagerzustand: New original, 3450 pcs Stock Available.</p>
	<p>Liefern von: Hong Kong</p>
	<p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>

Spezifikationen

Teilenummer	SI2327DS-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 200V 0.38A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	3450 pcs Stock
detaillierte Beschreibung	P-Channel 200V 380mA (Ta) 750mW (Ta) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	750mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	200V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	380mA (Ta)
Rds On (Max) @ Id, Vgs	2.35 Ohm @ 500mA, 10V
VGS (th) (Max) @ Id	4.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	12nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	510pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	6V, 10V
Vgs (Max)	±20V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2327DS-T1-E3CT

SI2327DS-T1-E3 ist neu im Original, Suche SI2327DS-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2327DS-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2327DS-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2325DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 150V 0.53A SOT-23</p>	 <p>SI2326DS-T1-GE3 VISHAY VISHAY SOT23</p>	 <p>SI2328DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V 1.15A SOT23-3</p>	 <p>SI2325DS-T1-GE3 Vishay / Siliconix MOSFET P-CH 150V 0.53A SOT-23</p>
 <p>SI2327DS-T1-E3 Vishay / Siliconix MOSFET P-CH 200V 0.38A SOT23-3</p>	 <p>SI2326DS-T1-E3 VISHAY VISHAY SOT23</p>	 <p>SI2327DS-T1-GE3 Vishay / Siliconix MOSFET P-CH 200V 0.38A SOT-23</p>	 <p>SI2328DS-T1 VISHAY SI2328DS-T1 VISHAY</p>

heiße Teile

Mehr

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|-------------------|--------------------|--------------------|--------------------|--------------------|
| ⊛ SI2320DS-T1-E3 | ↔ SI2320DS-T1-GE3 | ⇒ SI2321DS-T1-E3 | D SI2321DS-T1-E3 | ↔ SI2321DS-T1-GE3 |
| ↔ SI2321DS-T1-GE3 | ⊛ SI2323CDS-T1 | D SI2323CDS-T1-E3 | ⇒ SI2323CDS-T1-GE3 | ↔ SI2323CDS-T1-GE3 |
| ⊛ SI2323DDS-T1-E3 | ↔ SI2323DDS-T1-GE3 | ⊛ SI2323DDS-T1-GE3 | ↔ SI2323DS | ↔ SI2323DS-T1-E3 |
| D SI2323DS-T1-E3 | ⊛ SI2323DS-T1-GE3 | ↔ SI2323DS-T1-GE3 | ⊛ SI2324DS-T1-E3 | ↔ SI2324DS-T1-GE3 |
| ⇒ SI2324DS-T1-GE3 | ↔ SI2325DS-T1-E3 | ⊛ SI2325DS-T1-E3 | ↔ SI2325DS-T1-GE3 | ↔ SI2325DS-T1-GE3 |
| ↔ SI2327DS-T1-E3 | ⇒ SI2327DS-T1-GE3 | D SI2327DS-T1-GE3 | ⊛ SI2328DS | ↔ SI2328DS-T1 |
| ⊛ SI2328DS-T1-E3 | D SI2328DS-T1-E3 | ⇒ SI2328DS-T1-GE3 | ↔ SI2328DS-T1-GE3 | ↔ SI2329DS-T1-E3 |
| ↔ SI2329DS-T1-GE3 | ⊛ SI2329DS-T1-GE3 | ↔ SI2331DS | ⇒ SI2331DS-T1-E3 | ↔ SI2331DS-T1-E3 |
| ⊛ SI2331DS-T1-GE3 | ↔ SI2331DS-T1-GE3 | ⊛ SI2333ADS-T1-GE3 | D SI2333CDS | ↔ SI2333CDS-T1-E3 |
| ↔ SI2333CDS-T1-E3 | ⊛ SI2333CDS-T1-GE3 | ↔ SI2333CDS-T1-GE3 | ⊛ SI2333DDS-T1-E3 | ↔ SI2333DDS-T1-GE3 |

Contact us:Info@Y-IC.com

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